

IN THE CLAIMS

- 1 (Original). A method comprising:
positioning a conductive surface of a semiconductor wafer on a conductive polishing pad; and
providing electrical contact to said surface across the pad.
- 2 (Original). The method of claim 1 including providing a plurality of electrodes exposed through said pad.
- 3 (Original). The method of claim 2 including applying a potential of a first polarity to said conductive surface through said pad.
- 4 (Original). The method of claim 3 including coupling said electrodes to a potential of a second polarity opposite to the first polarity.
- 5 (Original). The method of claim 2 including providing circularly shaped openings in said pad over said electrodes.
- 6 (Original). The method of claim 1 including positioning said pad over a conductive platen.
- 7 (Original). The method of claim 5 including insulating said electrode from said pad.
- 8 (Original). The method of claim 1 including providing said pad over a conductive platen and applying potential to said film through said pad and platen.
- 9 (Original). The method of claim 1 including providing electrical contact to said surface over the entire extent of said surface.

10 (Original). The method of claim 1 including applying pressure between said surface and said pad.

11 (Original). The method of claim 1 including providing an abrasive fluid between said surface and said pad.

12 (Original). The method of claim 1 including counter rotating said pad and said surface.

Claims 13-19 (Canceled).